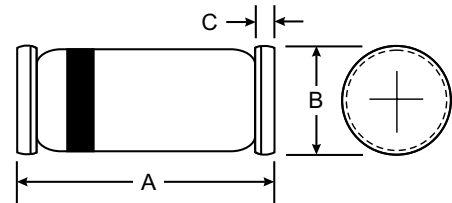


Features

- For general purpose applications
- These diodes feature very low turn-on voltage and fast switching. These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.



Mechanical Data

- Case: SOD-80(LL34), Glass
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.05 grams (approx.)



LL34/ SOD-80		
Dim	Min	Max
A	3.30	3.70
B	1.30	1.60
C	0.28	0.50
All Dimensions in mm		

Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	40	V
Continuous Forward Current	I_F	350 ⁽¹⁾	mA
Repetitive Peak Forward Current at $t_p < 1s$,	I_{FRM}	1 ⁽¹⁾	A
Forward Surge Current at $t_p < 10ms$,	I_{FSM}	7.5 ⁽¹⁾	A
Power Dissipation, $T_a = 65^\circ C$	P_D	330 ⁽¹⁾	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	300 ⁽¹⁾	$^\circ C/W$
Junction Temperature	T_J	125	$^\circ C$
Ambient Operating Temperature Range	T_a	-65 to + 125	$^\circ C$
Storage temperature range	T_s	-65 to + 150	$^\circ C$

Note: (1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature.

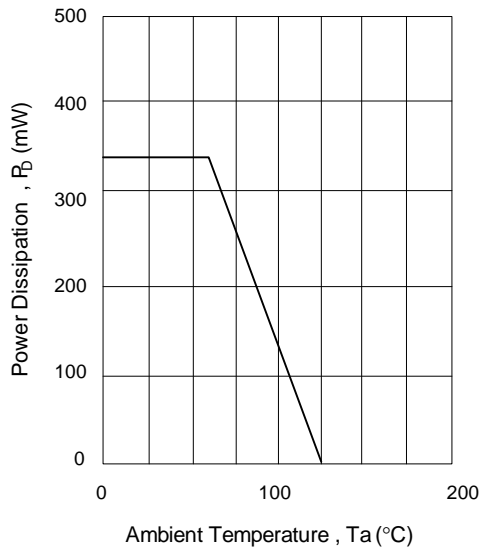
Electrical Characteristics ($T_J = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = 100 \mu A$ (pulsed)	40	-	-	V
Reverse Current Pulse Test $t_p < 300 \mu s$, $\delta < 2\%$	I_R	$V_R = 10V$ $V_R = 20V$ $V_R = 40V$	-	-	2 5 25	μA
Forward Voltage Pulse Test $t_p < 300 \mu s$, $\delta < 2\%$	V_F	$I_F = 1mA$ $I_F = 10mA$ $I_F = 30mA$ $I_F = 100mA$ $I_F = 500mA$	-	-	0.30 0.40 0.50 0.75 0.90	V
Diode Capacitance	Cd	$V_R = 1V$, $f = 1MHz$	-	12	-	pF

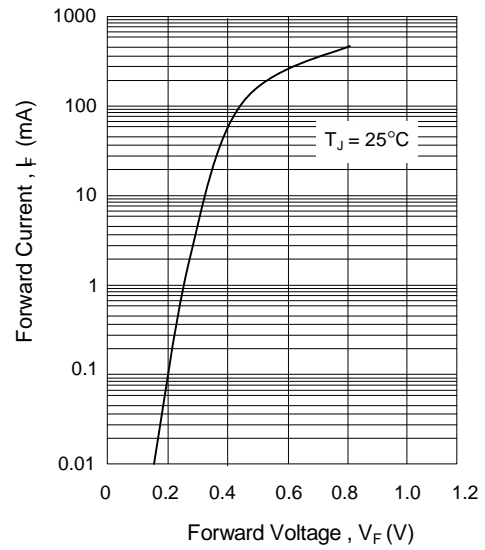


RATING AND CHARACTERISTIC CURVES (LL48)

Admissible Power Dissipation vs. Ambient Temperature



Typical Forward Characteristics



Typical Reverse Characteristics

